Dual Schottky Barrier Diodes

MBD110DWT1G, MBD330DWT1G

Application circuit designs are moving toward the consolidation of device count and into smaller packages. The new SOT−363 package is a solution which simplifies circuit design, reduces device count, and reduces board space by putting two discrete devices in one small six−leaded package. The SOT−363 is ideal for low−power surface mount applications where board space is at a premium, such as portable products.

Anode 1 ◦—▶|—◦ 6 Cathode
N/C 2 ◦   ◦ 5 N/C
Cathode 3 ◦—|◀—◦ 4 Anode

SC−88 / SOT−363
CASE 419B
STYLE 6

Surface Mount Comparisons:

	SOT−363	SOT−23
Area (mm^2)	4.6	7.6
Max Package P_D (mW)	120	225
Device Count	2	1

Space Savings:

Package	1 x SOT−23	2 x SOT−23
SOT−363	40%	70%

MARKING DIAGRAM

```
6  ▯ ▯ ▯
   ┌───────┐
   │ xx M ▪ │
   │ ◦   ▪  │
   └───────┘
1  ▯ ▯ ▯
```

xx = Device Code
     Refer to Ordering Table,
     page 2
M = Date Code
▪ = Pb−Free Package
(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

The MBD110DW and MBD330DW devices are spin−offs of our popular MMBD101LT1 and MMBD301LT1 SOT−23 devices. They are designed for high−efficiency UHF and VHF detector applications. Readily available to many other fast switching RF and digital applications.
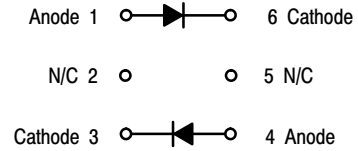
Features
- Extremely Low Minority Carrier Lifetime
- Very Low Capacitance
- Low Reverse Leakage
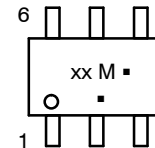- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating		Symbol	Value	Unit
Reverse Voltage	MBD110DWT1G MBD330DWT1G	V_R	7.0 30	V
Forward Current (DC)	MBD330DWT1G	I_F	200 Max	mA
Forward Power Dissipation $T_A = 25°C$		P_F	120	mW
Junction Temperature		T_J	−55 to +125	°C
Storage Temperature Range		T_{stg}	−55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Typ	Max	Unit
Reverse Breakdown Voltage (I_R = 10 µA) MBD110DWT1G MBD330DWT1G		$V_{(BR)R}$	7.0 30	10 –	– –	V
Diode Capacitance (V_R = 0, f = 1.0 MHz, Note 1) MBD110DWT1G		C_D	–	0.88	1.0	pF
Total Capacitance (V_R = 15 V, f = 1.0 MHz) MBD330DWT1G		C_T	–	0.9	1.5	pF
Reverse Leakage (V_R = 3.0 V) MBD110DWT1G (V_R = 25 V) MBD330DWT1G		I_R	– –	0.02 13	0.25 200	µA nA
Noise Figure (f = 1.0 GHz, Note 2) MBD110DWT1G		NF	–	6.0	–	dB
Forward Voltage (I_F = 10 mA) MBD110DWT1G (I_F = 1.0 mA) MBD330DWT1G (I_F = 10 mA)		V_F	– – –	0.5 0.38 0.52	0.6 0.45 0.6	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ORDERING INFORMATION

Device	Marking	Package	Shipping[†]
MBD110DWT1G	M4	SC−88 / SOT−363 (Pb−Free)	3000 Units / Tape & Reel
MBD330DWT1G	T4		

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

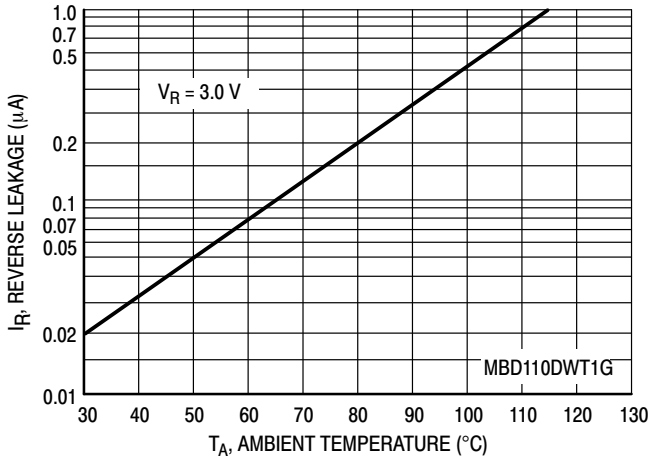## TYPICAL CHARACTERISTICS
MBD110DWT1G
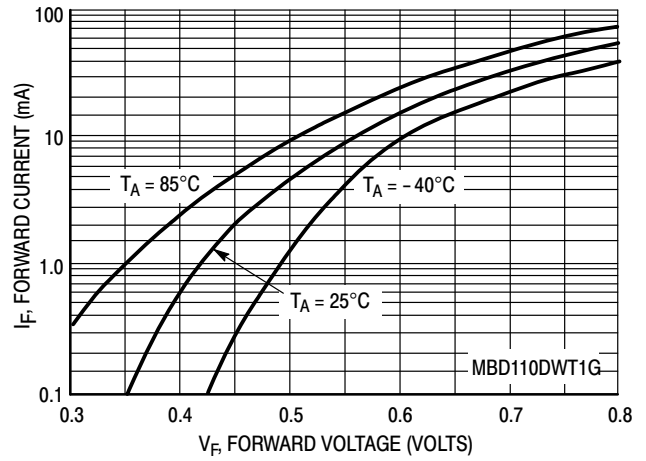

Figure 1. Reverse Leakage
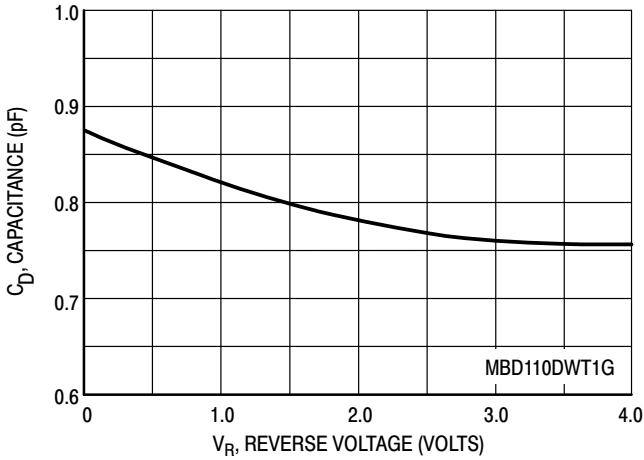

Figure 2. Forward Voltage
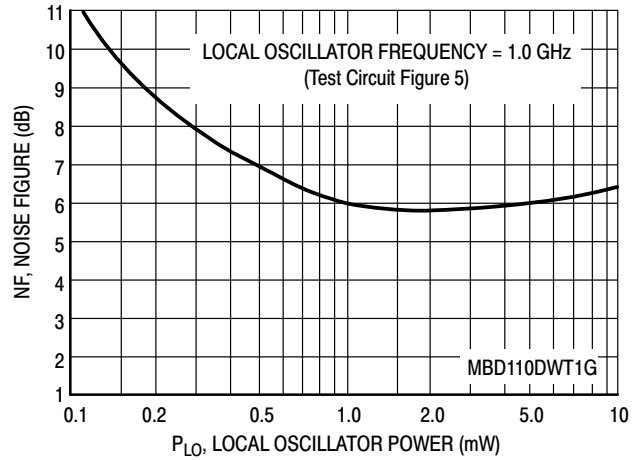

Figure 3. Capacitance
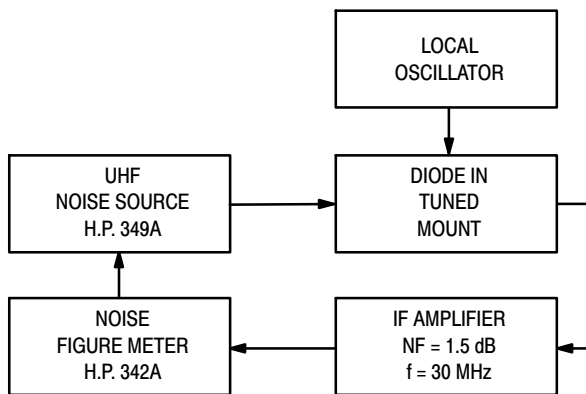

Figure 4. Noise Figure

Figure 5. Noise Figure Test Circuit

NOTES ON TESTING AND SPECIFICATIONS

Note 1 – C_D and C_T are measured using a capacitance bridge (Boonton Electronics Model 75A or equivalent).

Note 2 – Noise figure measured with diode under test in tuned diode mount using UHF noise source and local oscillator (LO) frequency of 1.0 GHz. The LO power is adjusted for 1.0 mW. IF amplifier NF = 1.5 dB, f = 30 MHz, see Figure 5.

Note 3 – L_S is measured on a package having a short instead of a die, using an impedance bridge (Boonton Radio Model 250A RX Meter).

TYPICAL CHARACTERISTICS
MBD330DWT1G
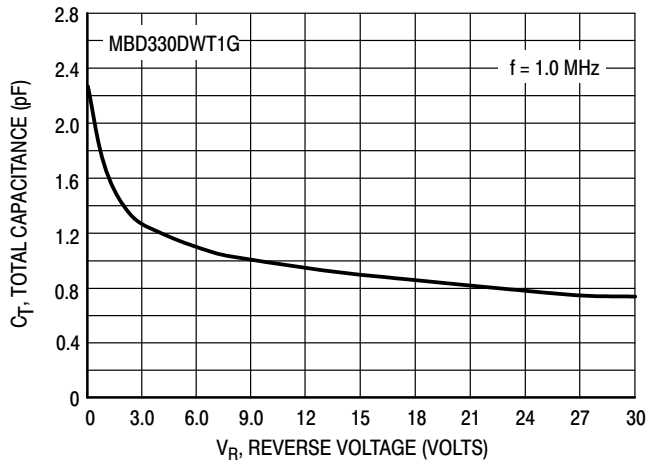
Figure 6. Total Capacitance
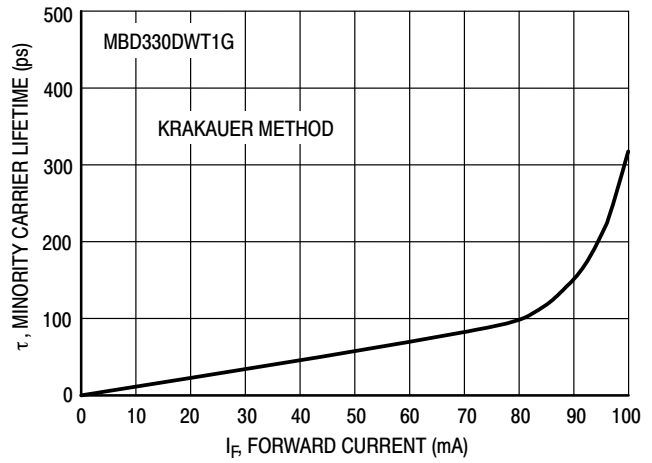
Figure 7. Minority Carrier Lifetime
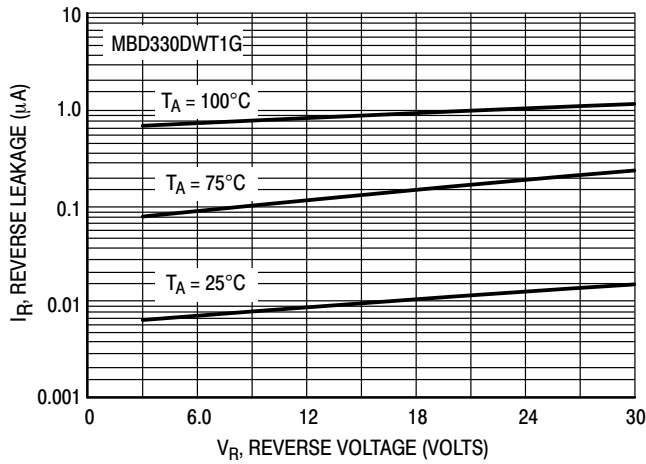
Figure 8. Reverse Leakage
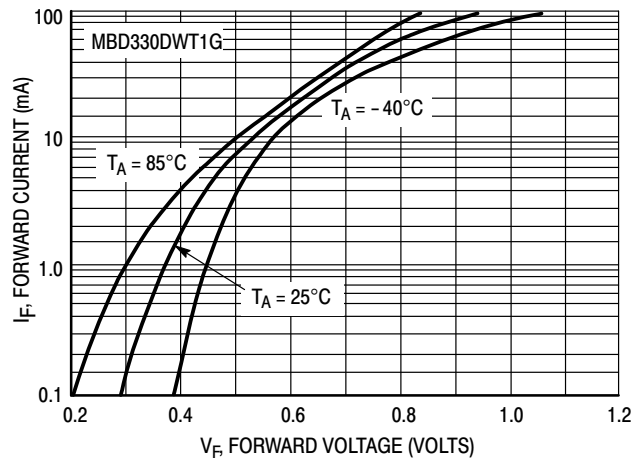
Figure 9. Forward Voltage

SC−88/SC70−6/SOT−363
CASE 419B−02
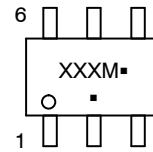ISSUE Y

1
SCALE 2:1

DATE 11 DEC 2012
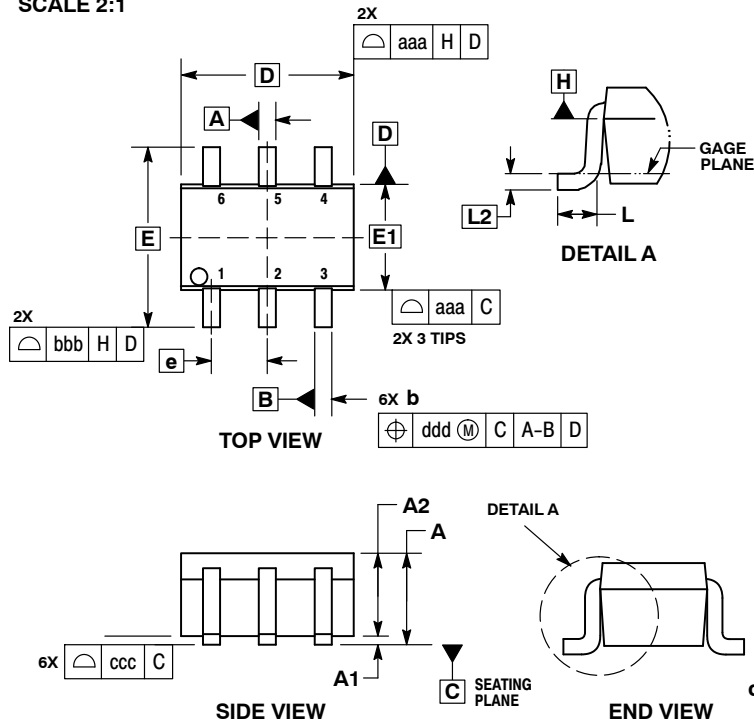
NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
4. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
5. DATUMS A AND B ARE DETERMINED AT DATUM H.
6. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
7. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION b AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

TOP VIEW

DETAIL A

SIDE VIEW

END VIEW

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	---	---	1.10	---	---	0.043
A1	0.00	---	0.10	0.000	---	0.004
A2	0.70	0.90	1.00	0.027	0.035	0.039
b	0.15	0.20	0.25	0.006	0.008	0.010
C	0.08	0.15	0.22	0.003	0.006	0.009
D	1.80	2.00	2.20	0.070	0.078	0.086
E	2.00	2.10	2.20	0.078	0.082	0.086
E1	1.15	1.25	1.35	0.045	0.049	0.053
e	0.65 BSC			0.026 BSC		
L	0.26	0.36	0.46	0.010	0.014	0.018
L2	0.15 BSC			0.006 BSC		
aaa	0.15			0.006		
bbb	0.30			0.012		
ccc	0.10			0.004		
ddd	0.10			0.004		

RECOMMENDED
SOLDERING FOOTPRINT*

6X
0.30

6X
0.66

2.50

0.65
PITCH

DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.
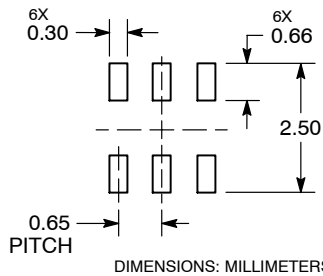
GENERIC
MARKING DIAGRAM*

6

XXXM■

1

XXX = Specific Device Code
M = Date Code*
■ = Pb−Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

DOCUMENT NUMBER:	98ASB42985B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	SC−88/SC70−6/SOT−363		PAGE 1 OF 2

SC−88/SC70−6/SOT−363
CASE 419B−02
ISSUE Y

DATE 11 DEC 2012

STYLE 1:
PIN 1. EMITTER 2
2. BASE 2
3. COLLECTOR 1
4. EMITTER 1
5. BASE 1
6. COLLECTOR 2

STYLE 2:
CANCELLED

STYLE 3:
CANCELLED

STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. COLLECTOR
4. EMITTER
5. BASE
6. ANODE

STYLE 5:
PIN 1. ANODE
2. ANODE
3. COLLECTOR
4. EMITTER
5. BASE
6. CATHODE

STYLE 6:
PIN 1. ANODE 2
2. N/C
3. CATHODE 1
4. ANODE 1
5. N/C
6. CATHODE 2

STYLE 7:
PIN 1. SOURCE 2
2. DRAIN 2
3. GATE 1
4. SOURCE 1
5. DRAIN 1
6. GATE 2

STYLE 8:
CANCELLED

STYLE 9:
PIN 1. EMITTER 2
2. EMITTER 1
3. COLLECTOR 1
4. BASE 1
5. BASE 2
6. COLLECTOR 2

STYLE 10:
PIN 1. SOURCE 2
2. SOURCE 1
3. GATE 1
4. DRAIN 1
5. DRAIN 2
6. GATE 2

STYLE 11:
PIN 1. CATHODE 2
2. CATHODE 2
3. ANODE 1
4. CATHODE 1
5. CATHODE 1
6. ANODE 2

STYLE 12:
PIN 1. ANODE 2
2. ANODE 2
3. CATHODE 1
4. ANODE 1
5. ANODE 1
6. CATHODE 2

STYLE 13:
PIN 1. ANODE
2. N/C
3. COLLECTOR
4. EMITTER
5. BASE
6. CATHODE

STYLE 14:
PIN 1. VREF
2. GND
3. GND
4. IOUT
5. VEN
6. VCC

STYLE 15:
PIN 1. ANODE 1
2. ANODE 2
3. ANODE 3
4. CATHODE 3
5. CATHODE 2
6. CATHODE 1

STYLE 16:
PIN 1. BASE 1
2. EMITTER 2
3. COLLECTOR 2
4. BASE 2
5. EMITTER 1
6. COLLECTOR 1

STYLE 17:
PIN 1. BASE 1
2. EMITTER 1
3. COLLECTOR 2
4. BASE 2
5. EMITTER 2
6. COLLECTOR 1

STYLE 18:
PIN 1. VIN1
2. VCC
3. VOUT2
4. VIN2
5. GND
6. VOUT1

STYLE 19:
PIN 1. I OUT
2. GND
3. GND
4. V CC
5. V EN
6. V REF

STYLE 20:
PIN 1. COLLECTOR
2. COLLECTOR
3. BASE
4. EMITTER
5. COLLECTOR
6. COLLECTOR

STYLE 21:
PIN 1. ANODE 1
2. N/C
3. ANODE 2
4. CATHODE 2
5. N/C
6. CATHODE 1

STYLE 22:
PIN 1. D1 (i)
2. GND
3. D2 (i)
4. D2 (c)
5. VBUS
6. D1 (c)

STYLE 23:
PIN 1. Vn
2. CH1
3. Vp
4. N/C
5. CH2
6. N/C

STYLE 24:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. CATHODE
6. CATHODE

STYLE 25:
PIN 1. BASE 1
2. CATHODE
3. COLLECTOR 2
4. BASE 2
5. EMITTER
6. COLLECTOR 1

STYLE 26:
PIN 1. SOURCE 1
2. GATE 1
3. DRAIN 2
4. SOURCE 2
5. GATE 2
6. DRAIN 1

STYLE 27:
PIN 1. BASE 2
2. BASE 1
3. COLLECTOR 1
4. EMITTER 1
5. EMITTER 2
6. COLLECTOR 2

STYLE 28:
PIN 1. DRAIN
2. DRAIN
3. GATE
4. SOURCE
5. DRAIN
6. DRAIN

STYLE 29:
PIN 1. ANODE
2. ANODE
3. COLLECTOR
4. EMITTER
5. BASE/ANODE
6. CATHODE

STYLE 30:
PIN 1. SOURCE 1
2. DRAIN 2
3. DRAIN 2
4. SOURCE 2
5. GATE 1
6. DRAIN 1

Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

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DESCRIPTION:	SC−88/SC70−6/SOT−363		PAGE 2 OF 2

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